YG803C06 (15A)

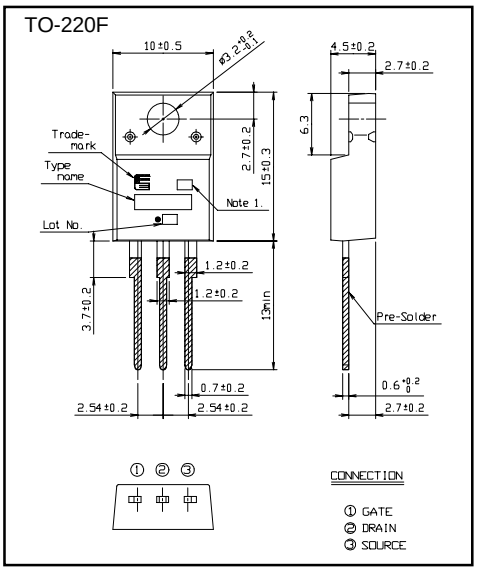
(60V / 15A)

Schottky barrier diode

■ Major characteristics

Characteristics	YG803C06	Units	Condition
V_{RRM}	60	V	
V_F	0.48	V	Tj=125°C, typ
Io	15	A	

■ Outline drawings, mm



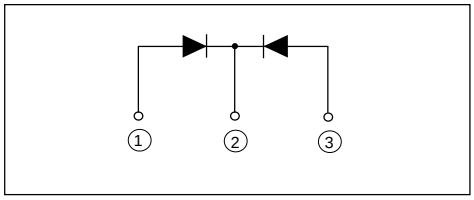
■ Features

- Low V_F
- Optimized for 3.3V
- 5V output application
- Center tap connection

■ Applications

- High frequency operation
- DC-DC converters
- AC adapter

■ Connection diagram



■ Maximum ratings and characteristics

● Absolute maximum ratings

Item	Symbol	Conditions	Rating	Unit
Repetitive peak surge reverse voltage	V_{RSM}	tw=500ns, duty=1/40	60	V
Repetitive peak reverse voltage	V_{RRM}		60	V
Isolating voltage	Viso	Terminals-to-Case, AC.1min	1500	V
Average output current	Io	Square wave, duty=1/2 Tc=94°C	15 *	A
Non-repetitive surge current	I_{FSM}	Sine wave 10ms, 1shot	100	A
Operating junction temperature	T_j		+150	°C
Storage temperature	T_{stg}		-40 to +150	°C

* Average output current at centertap full wave connection

● Electrical characteristics (Tc=25°C Unless otherwise specified)

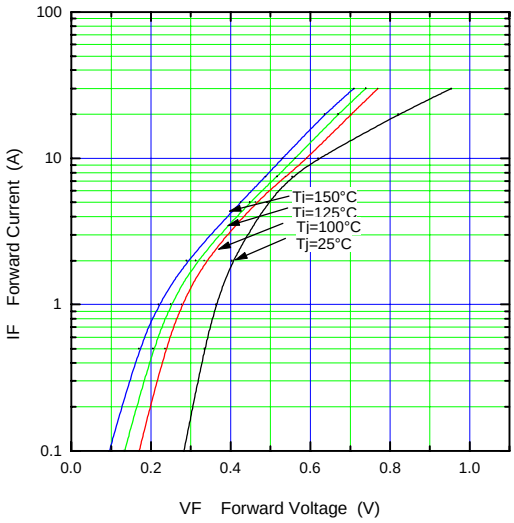
Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_F	I_{FM}=6A	0.58	V
Reverse current	I_R	V_R=V_{RRM}	5.0	mA

● Electrical characteristics (Tc=25°C Unless otherwise specified)

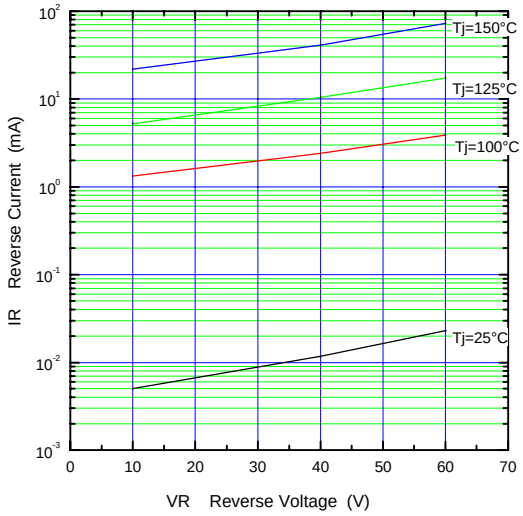
Item	Symbol	Condition	Max.	Unit
Thermal resistance	Rth(j-c)	Junction to case	3.0	°C/W

■ Characteristics

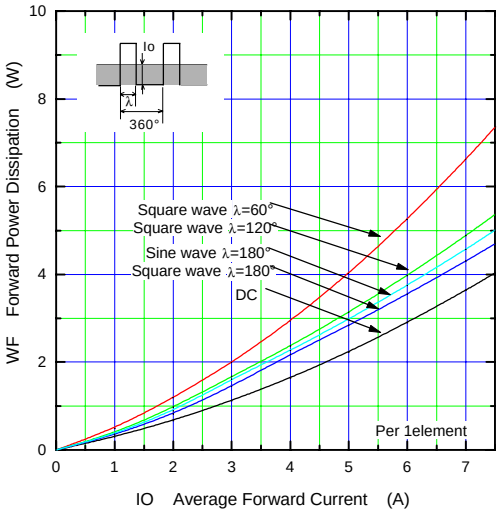
Forward Characteristic (typ.)



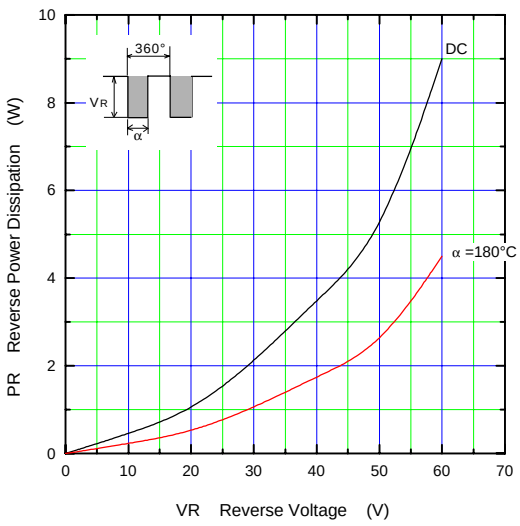
Reverse Characteristic (typ.)



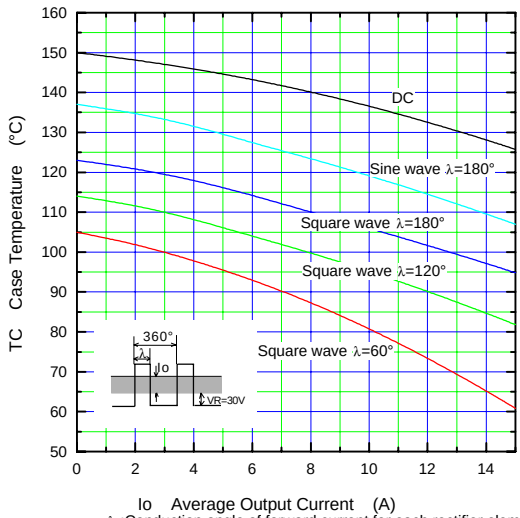
Forward Power Dissipation



Reverse Power Dissipation

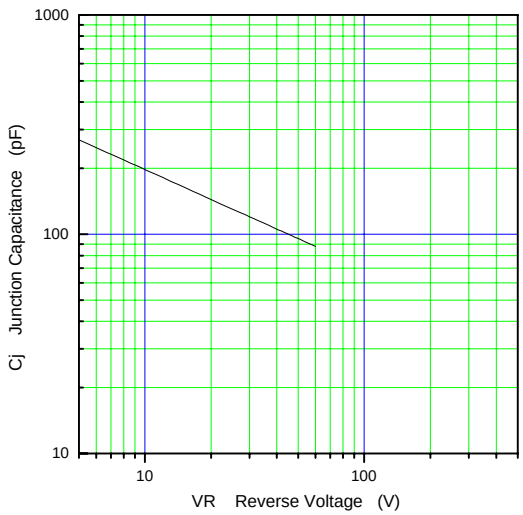


Current Derating (Io-Tc)

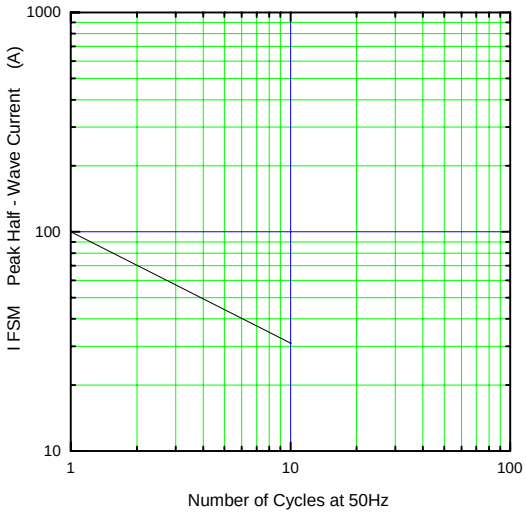


λ :Conduction angle of forward current for each rectifier element
Io:Output current of center-tap full wave connection

Junction Capacitance Characteristic(typ.)



Surge Capability



Transient Thermal Impedance